

**Amendments to the Claims:** This listing of claims will replace all prior versions, and listings, of claims in the application.

Listing of Claims:

1.-7. (Cancelled)

8. (Currently Amended) A semiconductor device having a titanium material layer and a silicon oxide layer ~~produced by a process including the step of:~~

~~etching at least one of the titanium material layer and the silicon oxide layer using an etchant, wherein~~

the titanium material layer includes at least one material selected from the group consisting of  $\text{BaTiO}_3$ ,  $\text{SrTiO}_3$ ,  $\text{Ba}_x\text{Sr}_{(1-x)}\text{TiO}_3$ , and similar Group IIA metal titanates, the titanium material layer is provided between an upper electrode and a lower electrode, ~~and a first contact window is provided for the lower electrode and a second contact window is provided on the titanium material layer for the upper electrode, wherein an interconnect material layer is provided over and inside each of the first and second contact windows, and the interconnect material layer that is provided over and inside the second contact window acts as an upper electrode;~~

wherein, when viewed from above the surface of the semiconductor device, the titanium material layer is arranged inside the lower electrode.

~~the etchant includes a mixed liquid of  $\text{HCl}$ ,  $\text{NH}_4\text{F}$  and  $\text{H}_2\text{O}$ ; and~~

~~setting a molar ratio of  $\text{NH}_4\text{F}/\text{HCl}$  in the mixed liquid, the molar ratio being set based on which of the at least one of the titanium material layer and the silicon oxide layer is to be etched.~~

9.-11. (Cancelled)

12. (New) The semiconductor device according to claim 8, wherein, when viewed from above the surface of the semiconductor device, the upper electrode is arranged inside the titanium material layer.